

N-channel SiC power MOSFET

V_{DSS}	1200V
R _{DS(on)} (Typ.)	80 m Ω
I _D	35A
P_D	179W

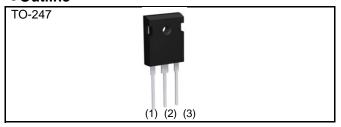
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

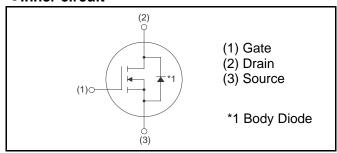
Application

- Solar inverters
- DC/DC converters
- Induction heating
- Motor drives

Outline



•Inner circuit



Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	-
	Marking	SCT2080KE

● Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	1200	V
Continuous drain current	T _c = 25°C	I _D *1	35	А
Continuous drain current	T _c = 100°C	I _D *1	22	А
Pulsed drain current		I _{D,pulse} *2	80	А
Gate - Source voltage		V_{GSS}	-6 to 22	V
Power dissipation (T _c = 25°C)		P _D	179	W
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	-	0.7	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

•Electrical characteristics ($T_a = 25$ °C)

Parameter	Cumbal	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	1200	-	-	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I _{DSS}	$T_j = 25^{\circ}C$	-	1	10	μΑ
		T _j = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}$, $I_D = 4.4 \text{mA}$	1.6	-	4.0	V
		$V_{GS} = 18V, I_D = 10A$				
Static drain - source on - state resistance	R _{DS(on)} *3	$T_j = 25$ °C	-	80	117	mΩ
		T _j = 125°C	-	125	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	6.3	-	Ω

•Electrical characteristics $(T_a = 25^{\circ}C)$

Darameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *3	$V_{DS} = 10V, I_{D} = 10A$	-	3.7	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	2080	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	77	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	ı	16	ı	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	116		pF
Turn - on delay time	t _{d(on)} *3	$V_{DD} = 400V, V_{GS} = 18V$	-	35	-	
Rise time	t _r *3	I _D = 10A	-	36	-	no
Turn - off delay time	t _{d(off)} *3	$R_L = 40\Omega$	-	76	-	ns
Fall time	t _f *3	$R_G = 0\Omega$	1	22	-	

•Gate Charge characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*3}	V _{DD} = 400V	-	106	ı	
Gate - Source charge	Q _{gs} *3	I _D = 10A	-	27	ı	nC
Gate - Drain charge	Q _{gd} *3	V _{GS} = 18V	-	31	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 400V, I_D = 10A$	-	9.7	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

^{*3} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai nietei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	-	25	А
Inverse diode direct current, pulsed	I _{SM} *2		-	-	80	А
Forward voltage	V _{SD} *3	$V_{GS} = 0V, I_{S} = 10A$	-	4.6	-	V
Reverse recovery time	t _{rr} *3		-	31	-	ns
Reverse recovery charge	Q _{rr} *3	I _F = 10A, V _R = 400V di/dt = 150A/μs	-	44	-	nC
Peak reverse recovery current	I _{rrm} *3		-	2.3	-	Α

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	0.098	
R _{th2}	0.237	K/W
R _{th3}	0.212	

Symbol	Value	Unit
C _{th1}	0.005	
C _{th2}	0.032	Ws/K
C _{th3}	0.666	

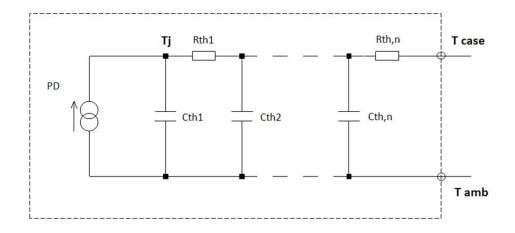


Fig.1 Power Dissipation Derating Curve

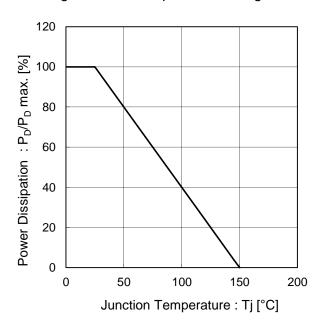


Fig.2 Maximum Safe Operating Area

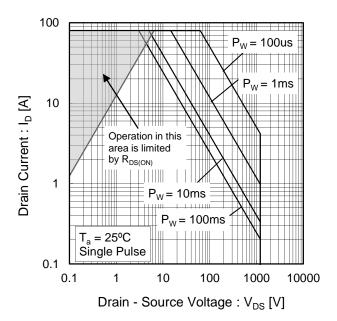


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

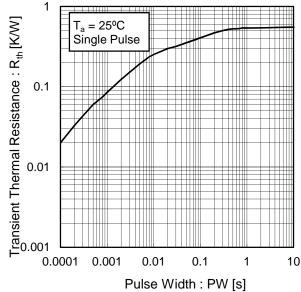


Fig.4 Typical Output Characteristics(I)

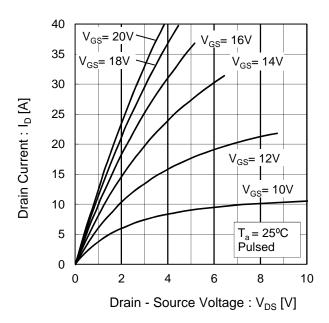


Fig.5 Typical Output Characteristics(II)

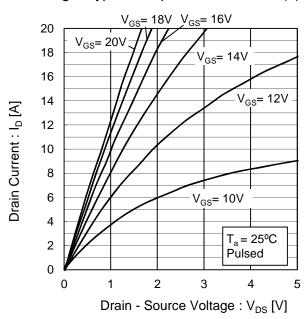


Fig.6 Typical Output Characteristics(I)

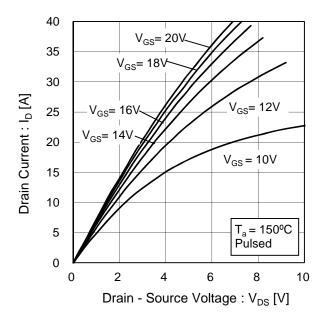


Fig.7 Typical Output Characteristics(II)

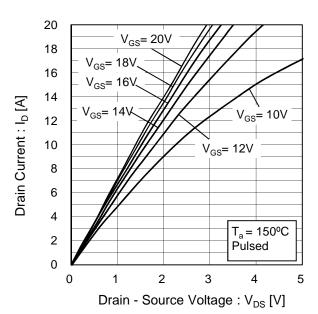
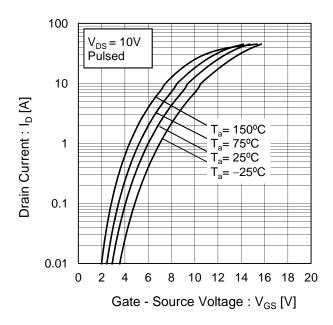


Fig.8 Typical Transfer Characteristics



vs. Junction Temperature 5 $V_{DS} = 10V$ 4.5 Gate Threshold Voltage : $V_{GS(th)}[V]$ $I_D = 10 \text{mA}$ 4 3.5 3 2.5 2 1.5 1 0.5 0 -50 0 50 100 150 Junction Temperature : T_i [°C]

Fig.9 Gate Threshold Voltage

Fig.10 Transconductance vs. Drain Current

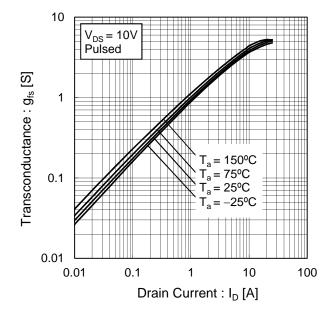


Fig.11 Static Drain - Source On - State Resistance vs. Gate - Source Voltage 8.0 Static Drain - Source On-State Resistance $T_a = 25^{\circ}C$ Pulsed 0.6 $:R_{DS(on)}\left[\Omega \right]$ 0.4 $I_{D} = 20A$ 0.2 $I_D = 10A$ 0 6 8 10 12 14 16 18 20 22 Gate - Source Voltage : V_{GS} [V]

Fig.12 Static Drain - Source On - State
Resistance vs. Junction Temperature

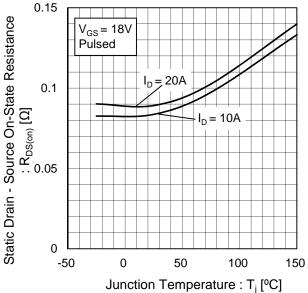


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current

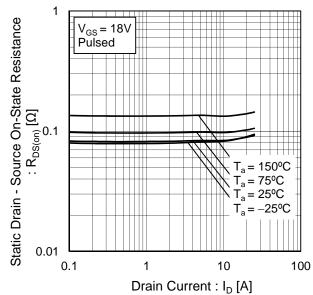


Fig.14 Typical Capacitance vs. Drain - Source Voltage

10000 C_{iss} 1000 C_{iss}

Fig.15 Coss Stored Energy

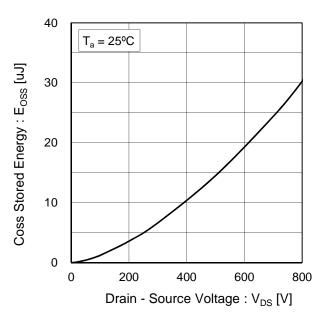


Fig.16 Switching Characteristics

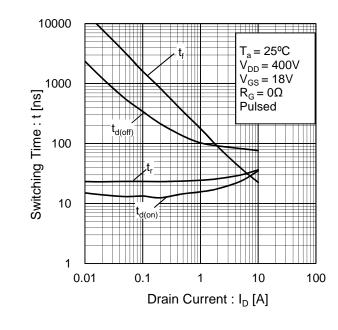
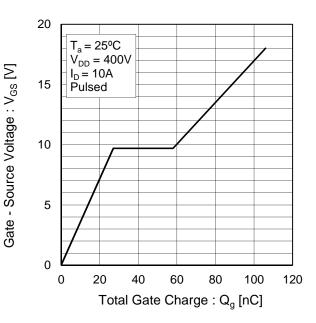
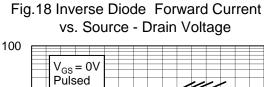


Fig.17 Dynamic Input Characteristics





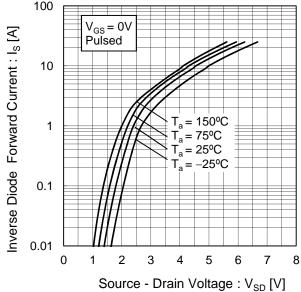
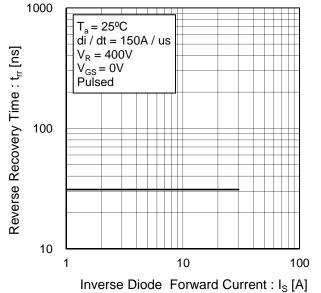


Fig.19 Reverse Recovery Time vs.Inverse Diode Forward Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

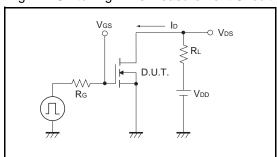


Fig.2-1 Gate Charge Measurement Circuit

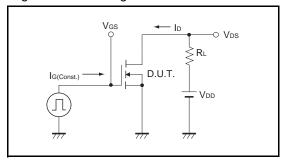


Fig.3-1 di/dt Measurement Circuit

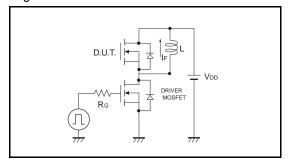


Fig.1-2 Switching Waveforms

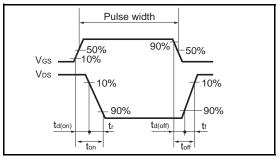


Fig.2-2 Gate Charge Waveform

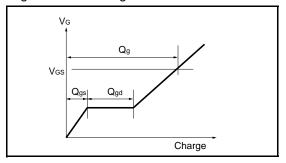
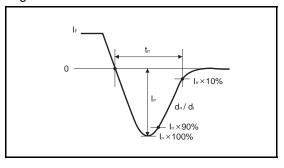
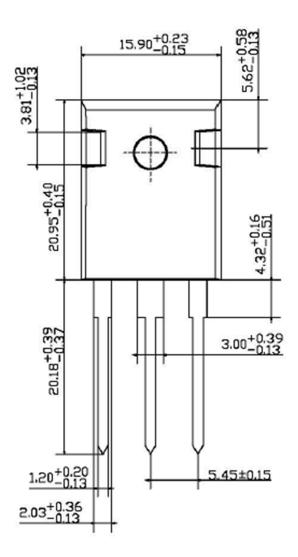


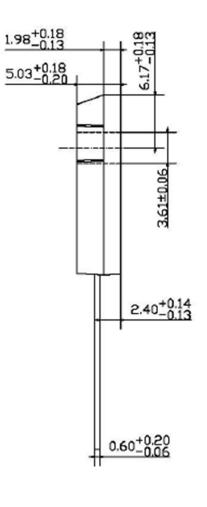
Fig.3-2 di/dt Waveform

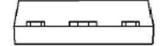


●Dimensions (Unit : mm)

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